



ACADEMIC LESSION PLAN FOR WINTER - 2023

Dept. of Electronics & Telecommunication, Govt. Polytechnic , Balasore

Name of the Faculty: Yogasakti Yogamaya (Lecturer, E&TC)

Subject: VLSI & Embedded System

Theory : 4 P/W
 Total Periods : 60 P/ Sem
 Examination : 3 Hours
 Sem : 5 E&TC

Internal Assessment : 20 Marks
 End Semester Exam : 80marks
 TOTAL MARKS : 100 Marks
 Start of Class : 1.08.2023

WEEK	PERIOD	TOPIC			
1st	1 st	Unit-1: Introduction to VLSI & MOS Transistor(12) 1.1 Historical perspective- Introduction	12		
	2 nd	1.2 Classification of CMOS digital circuit types			
	3 rd	1.3 Introduction to MOS Transistor& Basic operation of MOSFET.			
	4 th	1.4 Structure and operation of MOSFET (n-MOS enhancement type) & COMS			
2 nd	1 st	1.5 MOSFET V-I characteristics,		10	
	2 nd	1.6 Working of MOSFET capacitances.			
	3 rd	1.7 Modelling of MOS Transistors including Basic concept the SPICE level-1 models, the level-2 and level-3 model.			
	4 th	1.8 Flow Circuit design procedures			
3 rd	1 st	1.9 VLSI Design Flow & Y chart			9
	2 nd	1.10 Design Hierarchy			
	3 rd	1.11 VLSI design styles-FPGA, Gate Array Design,			
	4 th	Standard cells based, Full custom			
4 th	1 st	Unit-2: Fabrication of MOSFET (10) 2.1 Simplified process sequence for fabrication	9		
	2 nd	2.2 Basic steps in Fabrication processes Flow			
	3 rd	2.3 Fabrication process of nMOS Transistor			
	4 th	2.4 CMOS n-well Fabrication Process Flow			
5 th	1 st	2.5 MOS Fabrication process by n-well on p-substrate		9	
	2 nd	2.6 CMOS Fabrication process by P-well on n-substrate			
	3 rd	2.7 Layout Design rules			
	4 th	2.8 Stick Diagrams of CMOS inverter			
6 th	1 st	Unit-3:MOS Inverter(09) 3.1 Basic nMOS inverters,			9
	2 nd	3.2 Working of Resistive-load Inverter			
	3 rd	3.3 Inverter with n-Type MOSFET Load – Enhancement Load,			
	4 th	Depletion n-MOS inverter			
7 th	1 st	3.4 CMOS inverter – circuit operation and :	9		
	2 nd	characteristics and interconnect effects Delay time definitions			
	3 rd	3.5 CMOS Inventor design with delay constraints Two sample mask lay out for p-type substrate.			

	4 th	Unit-4: Static Combinational, Sequential, Dynamics logic circuits & Memories(15) 4.1 Define Static Combinational logic ,working of Static CMOS logic circuits (Two-input NAND Gate)
8 th	1 st	4.2 CMOS logic circuits (NAND2 Gate)
	2 nd	4.3 CMOS Transmission Gates(Pass gate)
	3 rd	4.4 Complex Logic Circuits - Basics
	4 th	4.5 Classification of Logic circuits based on their temporal behaviour
9 th	1 st	Continue
	2 nd	4.6 SR Flip latch Circuit,
	3 rd	Continue
	4 th	4.7 Clocked SR latch only.
10 th	1 st	Continue
	2 nd	4.8 CMOS D latch.
	3 rd	4.9 Basic principles of Dynamic Pass Transistor Circuits
	4 th	4.10 Dynamic RAM,
11 th	1 st	SRAM,
	2 nd	4.11 Flash memory
	3 rd	Unit-5: System Design method & synthesis (04) 5.1 Design Language (SPL & HDL)& HDL & EDA tools
	4 th	VHDL and packages Xlinx
12 th	1 st	5.2 Design strategies
	2 nd	concept of FPGA with standard cell based design
	3 rd	VHDL for design synthesis using CPLD or FPGA
	4 th	5.3 VHDL for design synthesis using CPLD or FPGA
13 th	1 st	5.4 Raspberry Pi - Basic idea
	2 nd	5.4 Raspberry Pi - Basic idea
	3 rd	Unit-6: Introduction to Embedded Systems(10) 6.1 Embedded Systems Over view ,list of embedded systems, characteristics ,
	4 th	example – A Digital Camera
14 th	1 st	6.2 Embedded Systems Technologies--Technology – Definition. -Technology for Embedded Systems
	2 nd	Processor Technology, IC Technology
	3 rd	6.3 Design Technology-Processor Technology, General Purpose Processors – Software,
	4 th	Basic Architecture of Single Purpose Processors – Hardware
15 th	1 st	6.4 Application – Specific Processors, Microcontrollers, Digital Signal Processors(DSP)
	2 nd	6.5 IC Technology- Full Custom / VLSI, Semi-Custom ASIC
	3 rd	(Gate Array & Standard Cell), PLD (Programmable Logic Device)
	4 th	6.6 Basic idea of Arduino micro controller

4/11/8/23

5/11/23